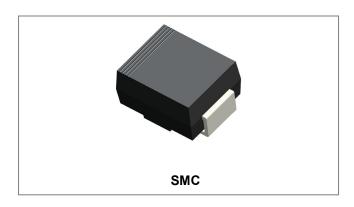






#### SK520 SCHOTTKY RECTIFIER



#### **Features**

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Circuit Diagram**



#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- · Reverse battery protection

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	200	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>A</sub> =105°C, rectangular wave form (Note 1)	5	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>C</sub> = 25 °C	110	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 5A, Pulse, T <sub>J</sub> = 25 °C	0.85	1.10	V
	V <sub>F2</sub>	@ 5A, Pulse, T <sub>J</sub> = 125 °C	0.74	0.90	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R,</sub> T <sub>J</sub> = 25 °C	0.0002	1	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R,</sub> T <sub>J</sub> = 125 °C	0.05	7	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 \text{ °C}, f_{SIG} = 1MHz$	140	200	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

Note:1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.







### **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{ heta JA}$	DC operation	10	°C/W
Approximate Weight	wt	-	0.21	g

# **Ratings and Characteristics Curves**

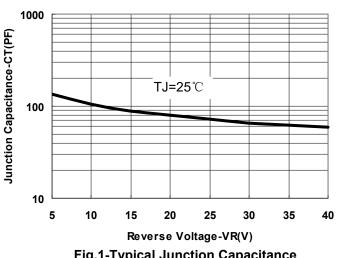


Fig.1-Typical Junction Capacitance

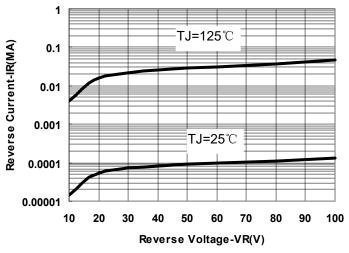


Fig.2-Typical Values Of Reverse Current

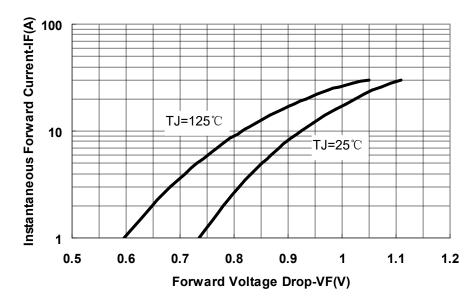


Fig.3-Typical Forward Voltage Drop Characteristics

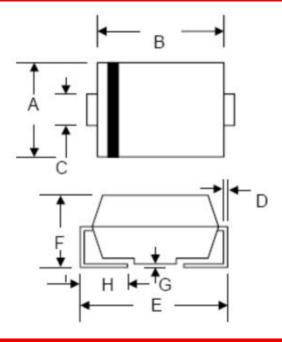
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## **Mechanical Dimensions SMC**



CYMPOL	Millin	neters	Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	5.59	6.22	0.220	0.245	
В	6.60	7.11	0.260	0.280	
С	2.75	3.25	0.108	0.128	
D	0.152	0.305	0.006	0.012	
E	7.75	8.25	0.305	0.325	
F	2.00	2.95	0.079	0.116	
G	0.051	0.203	0.002	0.008	
Н	0.76	1.60	0.030	0.063	

# **Ordering Information**

Device Package		Shipping	
SK520	SMC (Pb-Free)	3000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



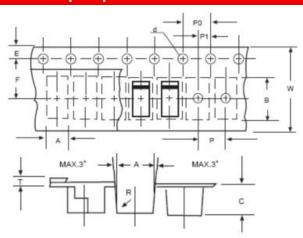
Where XXXXX is YYWWL

SK = Device Type
5 = Forward Current (5A)
20 = Reverse Voltage (200V)
YY = Year

WW = Week L = Lot Number

**Cautions:** Molding resin Epoxy resin UL:94V-0

# **Carrier Tape Specification SMC**



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	5.90	6.10	
В	8.20	8.40	
C	2.40	2.60	
d	1.40	1.60	
E	1.40	1.60	
F	7.60	7.70	
Р	7.90	8.10	
P0	3.90	4.10	
P1	3.90	4.10	
Т	-	0.600	
W	15.80	16.20	

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